The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-3. (Canceled)

4. (Currently Amended) A device having at least one display panel, said display panel having a plurality of pixels, each of which comprising:

~~at least first and second~~ a thin film ~~transistors~~ transistor formed over a glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate~~, said first signal line comprising aluminum~~;

an interlayer insulating film covering said ~~first and second~~ thin film ~~transistors~~ transistor;

a lead electrode comprising aluminum formed over said interlayer insulating film and electrically connected to one of the source or drain regions of ~~at least one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor through a hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising aluminum and electrically connected to the other one of the source or drain regions of said ~~at least one of said first and second~~ thin film ~~transistors~~ transistor;

an organic resin film formed over the ~~first and second~~ thin film ~~transistors~~ transistor, said interlayer insulating film, and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film,

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

5.-8. (Canceled)

9. (Currently Amended) A television comprising:

a tuner for receiving television radio wave;

a display panel operationally connected to said tuner, said display panel having a plurality of pixels, each of which comprising:

~~at least first and second~~ a thin film ~~transistors~~ transistor formed over a glass substrate, ~~each of said first and second~~ said thin film ~~transistors~~ transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate~~, said first signal line comprising aluminum~~;

an interlayer insulating film covering said ~~first and second~~ thin film ~~transistors~~ transistor;

a lead electrode comprising aluminum formed over said interlayer insulating film and electrically connected to one of the source or drain regions of ~~at least one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor through a hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising

aluminum and electrically connected to the other one of the source or drain regions of said ~~at least one of the first and second~~ thin film ~~transistors~~ transistor;

an organic resin film formed over the ~~first and second~~ thin film ~~transistors~~ transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film,

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

10.-13. (Canceled)

14. (Currently Amended) A portable computer having a display panel, said display panel having a plurality of pixels, each of which comprising:

~~at least first and second~~ a thin film ~~transistors~~ transistor formed over a glass substrate, ~~each of~~ said ~~first and second~~ thin film ~~transistors~~ transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate~~, said first signal line comprising aluminum~~;

an interlayer insulating film covering said ~~first and second~~ thin film ~~transistors~~ transistor;

a lead electrode comprising aluminum formed over said interlayer insulating film and electrically connected to one of the source or drain regions of ~~at least one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor through a hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising

aluminum and electrically connected to the other one of the source or drain regions of said ~~at least one of the first and second~~ thin film ~~transistors~~ transistor;

an organic resin film formed over the ~~first and second~~ thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film,

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

15.-24. (Canceled)

25. (Currently Amended) A device having at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line ~~comprising aluminum and~~ being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising aluminum and electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode and through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

26.-32. (Canceled)

33. (Currently Amended) A device having at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one semiconductor layer formed over said substrate and comprising at least a channel region, source and drain regions with said channel region therebetween;

a gate insulating film adjacent to said channel region;

a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line ~~comprising aluminum and~~ being contiguous to said gate electrode;

an insulating film over at least said semiconductor layer;

a lead electrode comprising aluminum formed over said insulating film and electrically connected to one of the source or drain regions through a first hole of said insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising aluminum and electrically connected to the other one of the source or drain regions;

an organic resin film over said insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said lead electrode through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said semiconductor layer.

34.-35. (Canceled)

36. (Previously Presented) The device according to claim 4 wherein said display panel is a liquid crystal device.

37. (Previously Presented) The television according to claim 9 wherein said display panel is a liquid crystal device.

38. (Previously Presented) The portable computer according to claim 14 wherein said display panel is a liquid crystal device.

39.-42. (Canceled)

43. (Previously Presented) The device according to claim 25 wherein said display panel is a liquid crystal device.

44.-50. (Canceled)

51. (Previously Presented) The device according to claim 33 wherein said display panel is a liquid crystal device.

52.-53. (Canceled)

54. (Currently Amended) The device according to claim 4 wherein ~~one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor is an N-channel transistor ~~and the other one of the first and second thin film transistors is~~ or a P-channel transistor.

55. (Currently Amended) The device according to claim 4 wherein the gate ~~electrodes~~ electrode of the ~~first and second~~ thin film ~~transistors are~~ transistor is connected to the first signal line.

56. (Currently Amended) The device according to claim 4 wherein said pixel electrode is electrically connected to said ~~first and second~~ thin film ~~transistors~~ transistor.

57. (Currently Amended) The television according to claim 9 wherein ~~one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor is an N-channel transistor ~~and the other one of the first and second thin film transistors is~~ or a P-channel transistor.

58. (Currently Amended) The television according to claim 9 wherein the gate ~~electrodes~~ electrode of the ~~first and second~~ thin film ~~transistors are~~ transistor is connected to the first signal line.

59. (Currently Amended) The television according to claim 9 wherein said pixel electrode is electrically connected to said ~~first and second~~ thin film ~~transistors~~ transistor.

60. (Currently Amended) The portable computer according to claim 14 wherein ~~one of~~ said ~~first and second~~ thin film ~~transistors~~ transistor is an N-channel transistor ~~and the other one of the first and second thin film transistors is~~ or a P-channel transistor.

61. (Currently Amended) The portable computer according to claim 14 wherein the gate ~~electrodes~~ electrode of the ~~first and second~~ thin film ~~transistors are~~ transistor is connected to the first signal line.

62. (Currently Amended) The portable computer according to claim 14 wherein said pixel electrode is electrically connected to said ~~first and second~~ thin film ~~transistors~~ transistor.

63. (Previously Presented) A semiconductor device comprising:

a substrate;

at least first and second thin film transistors provided over the substrate;

a first signal line extending in a first direction over the substrate wherein gate electrodes of the first and second thin film transistors are connected to the first signal line;

a second signal line extending across said first signal line wherein said second signal line is connected to one of source or drain of the first thin film transistor and one of source or drain of the second thin film transistor;

an organic resin film formed over the first and second thin film transistors and the first and second signal lines; and

a pixel electrode over the organic resin film wherein the pixel electrode is electrically connected to the other one of the source or drain of the first thin film transistor and the other one of the source or drain of the second thin film transistor,

wherein the first and second thin film transistors are disposed with the second signal line located therebetween.

64. (Previously Presented) The semiconductor device according to claim 61 wherein the first thin film transistor is an N-channel thin film transistor and the second thin film transistor is a P-channel thin film transistor.

65. (Previously Presented) A semiconductor device comprising:

a substrate;

at least first and second thin film transistors provided in one pixel over the substrate;

a pixel electrode provided in the pixel;

a first signal line for selecting said pixel;

a second signal line for supplying a signal to the pixel electrode; and

an organic resin film formed over the first and second signal lines,

wherein the first and second thin film transistors are disposed with the second signal line located therebetween.

66. (Previously Presented) The semiconductor device according to claim 63 wherein the first thin film transistor is an N-channel thin film transistor and the second thin film transistor is a P-channel thin film transistor.

67. (New) A computer comprising at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one thin film transistor formed over said glass substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a first hole of said interlayer insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising aluminum and electrically connected to the other one of the source or drain regions;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode and through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said thin film transistor.

68. (New) A computer having at least one display device, said display device comprising:

a glass substrate having an insulating surface;

at least one semiconductor layer formed over said substrate and comprising at least a channel region, source and drain regions with said channel region therebetween;

a gate insulating film adjacent to said channel region;

a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

a first signal line extending in a first direction over said substrate, said first signal line being contiguous to said gate electrode;

an insulating film over at least said semiconductor layer;

a lead electrode comprising aluminum formed over said insulating film and electrically connected to one of the source or drain regions through a first hole of said insulating film;

a second signal line formed over said interlayer insulating film and extending in a second direction orthogonal to said first direction, said second signal line comprising aluminum and electrically connected to the other one of the source or drain regions;

an organic resin film over said insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said lead electrode through a second hole of the organic resin film,

wherein the first hole and the second hole do not overlap to each other, and

wherein a blocking film comprising silicon oxide is interposed between said glass substrate and said semiconductor layer.